



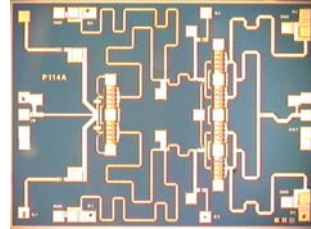
# EMP114

ISSUED DATE: 09-09-04

## 7.0 – 9.0 GHz Power Amplifier MMIC

### FEATURES

- 7.0 – 9.0 GHz Operating Frequency Range
- 30.0dBm Output Power at 1dB Compression
- 19.0 dB Typical Small Signal Gain
- -40dBc OIMD3 @Each Tone Pout 20dBm



Dimension: 2000um X 2650um  
Thickness: 75um ± 13um

### APPLICATIONS

- Point-to-point and point-to-multipoint radio
- Military Radar Systems



Caution! ESD sensitive device.

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C, 50 ohm, V<sub>DD</sub>= 7 V, I<sub>DQ</sub>= 800 mA)

SYMBOL	PARAMETER/TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>F</b>	Operating Frequency Range	7.0		9.0	GHz
<b>P1dB</b>	Output Power at 1dB Gain Compression	28.5	30.0		dBm
<b>G<sub>ss</sub></b>	Small Signal Gain	16.0	19.0		dB
<b>OIMD3</b>	Output 3 <sup>rd</sup> Order Intermodulation Distortion @Δf=10MHz, Each Tone Pout 20dBm		-40		dBc
<b>Input RL</b>	Input Return Loss		-12		dB
<b>Output RL</b>	Output Return Loss		-6		dB
<b>I<sub>dss</sub></b>	Saturate Drain Current V <sub>DS</sub> =3V, V <sub>GS</sub> =0V	992	1240	1488	mA
<b>V<sub>DD</sub></b>	Power Supply Voltage		7	8	V
<b>R<sub>th</sub></b>	Thermal Resistance (Au-Sn Eutectic Attach)		7.5		°C/W
<b>T<sub>b</sub></b>	Operating Base Plate Temperature	- 35		+ 85	°C

### ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION<sup>1,2</sup>

SYMBOL	CHARACTERISTIC	VALUE
V <sub>DS</sub>	Drain to Source Voltage	8 V
V <sub>GS</sub>	Gate to Source Voltage	- 4 V
I <sub>DD</sub>	Drain Current	I <sub>dss</sub>
I <sub>GSF</sub>	Forward Gate Current	18 mA
P <sub>IN</sub>	Input Power	@ 3dB compression
T <sub>CH</sub>	Channel Temperature	150°C
T <sub>STG</sub>	Storage Temperature	-65/150°C
P <sub>T</sub>	Total Power Dissipation	15.2W

1. Operating the device beyond any of the above rating may result in permanent damage.

2. Bias conditions must also satisfy the following equation  $V_{DS} \cdot I_{DS} < (T_{CH} - T_{HS})/R_{TH}$ ; where T<sub>HS</sub> = ambient temperature

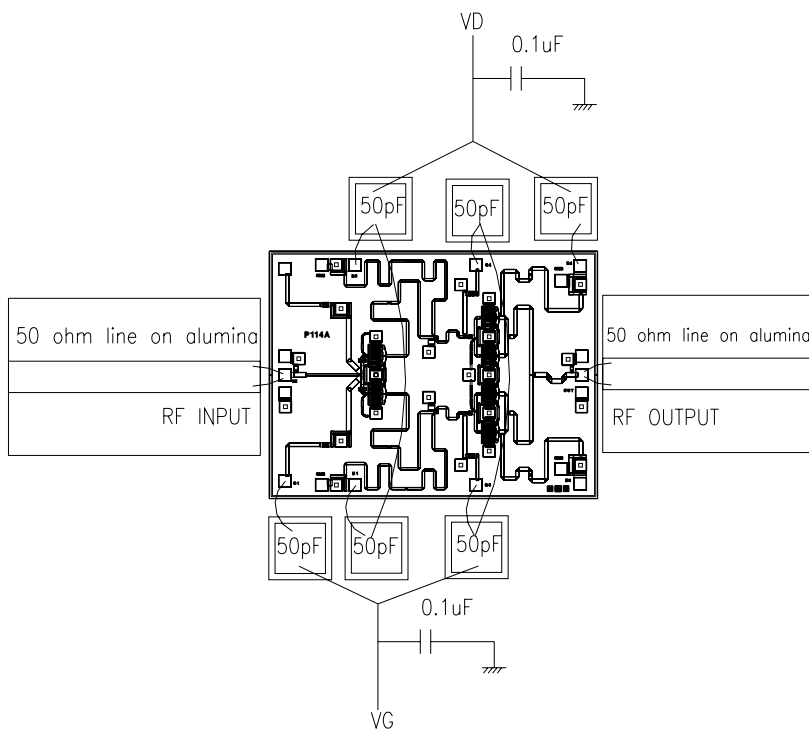
Specifications are subject to change without notice.



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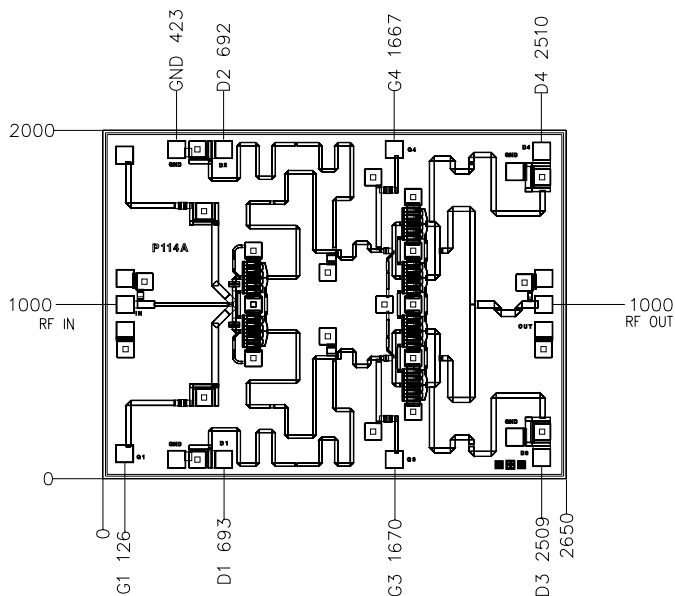
## PRELIMINARY DATA SHEET ASSEMBLY DRAWING

## 7.0 – 9.0 GHz Power Amplifier MMIC



The length of RF wires should be as short as possible. Use at least two wires between RF pad and 50 ohm line and separate the wires to minimize the mutual inductance.

### CHIP OUTLINE



Chip Size 2000 x 2650 microns  
Chip Thickness: 75 ± 13 microns  
PAD Dimensions: 100 x 100 microns  
All Dimensions in Microns

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page 2 of 2  
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